Solution to Exercise 2.1-1

Derive and discuss numbers for μ and v_D

- First Task: Derive numbers for the mobility μ.
 - First we need typical conductivities and electron densities in metals, which we can take from the table in the link.
 - At the same time we expand the table a bit

Material	ρ [Ω cm]	σ [Ω ⁻¹ cm ⁻¹]	Density <i>d</i> [10 ³ kg m ⁻³]	Atomic weight <i>w</i> [1u = 1.66 · 10 $^{-27}$ kg]	n = d/w [m ⁻³]
Silver (Ag)	1.6·10 ⁻⁶	6.2·10 ⁵	10.49	107.9	5.85 · 10 ²⁸
Copper (Cu)	1.7·10 ⁻⁶	5.9·10 ⁵	8.92	63.5	8.46 · 10 ²⁸
Lead (Pb)	21.10 ⁻⁶	4.8·10 ⁴	11.34	207.2	3.3 · 10 ²⁸

For the mobility **µ** we have the equation

$$\mu = \frac{\sigma}{q \cdot n}$$

With q = elementary charge = 1.60 10^{-19} C and the density of electrons = density of atoms n calculated above, we obtain, for example for μ_{Aq}

$$\mu_{Ag} = \frac{6.2 \cdot 10^5}{1.6 \cdot 10^{-19} \cdot 5.85 \cdot 10^{28}} \frac{m^3}{C \cdot \Omega \cdot cm} = \frac{cm^2}{C \cdot \Omega}$$

The unit is a bit strange, but rembering that $1 C = 1 A \cdot 1 s$ and $1 \Omega = 1 V / 1 A$, we obtain

$$\mu_{Ag} = 66.2 \frac{cm^2}{Vs}$$

$$\mu_{Cu} = 43.6 \frac{cm^2}{Vs}$$

$$\mu_{Pb} = 9.1 \frac{cm^2}{Vs}$$

$$Vs$$

The mobility µ was defined as

$$\mu = \frac{v_D}{E}$$
or
$$v_D = \mu \cdot E$$

So what is a reasonable field strength in a metal?

Easy. Consider a cube with side length I = 1 cm. Then, the relevant area is F = 1 cm², and its resistance R is given by

$$R = \frac{\rho \cdot I}{F} = \rho [\Omega]$$

- A Cu or Ag cube thus would have a resistance of about 1.5 ·10⁻⁶ Ω. Applying a voltage of 1 V, or equivalently a field strength of 1 V/cm thus produces a current of $I = U/R \approx 650~000$ A or a current density of j = 650~000 A/cm²
- That seems to be an awfully large current. Yes, but it is the kind of current density encountered in integrated circuits! Think about it!
- Nevertheless, the wires in your house carry at most about **30 A** (above that the fuse blows) with a cross section of about **1 mm²**; so a reasonable current density is **3000 A/cm²**, which we will get for about $U = 1.5 \cdot 10^{-6} \Omega \cdot 3000 A = 4.5 \text{ mV}$.
- For a rough estimate we then take a field strength of 5 mV/cm and a mobility of 50 cm²/Vs and obtain

$$v_{D} = \frac{50}{\cdot} \frac{cm^{2}}{0.25} = \frac{cm}{s} = \frac{mm}{2.5}$$

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That should come as some surprise! The electrons only have to move very slowly on average in the current direction (or rather, due to sign conventions, against it).

- Is that true, or did we make a mistake?
- It *is* true! However, it does *not* mean that electrons will not run around like crazy inside the crystal, at very high speeds. It only means that their *net* movement in current (anti-)direction is very slow.
- Think of an single fly in a fly swarm (even better, <u>read the module</u> that discusses this analogy in detail). The flies are flying around at high speed like crazy but the fly swarm is not going anywhere as long as it stays in place. There is then no drift velocity and no net fly current!